Supporting Information for:

Controlled Hysteresis of Conductance in Molecular Tunneling Junctions

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Materials and Methods

We followed previously reported procedures for the preparation of materials and experimental methods, and included a description of the experiments that were conducted in the same way.

Materials

All reagents were used as supplied unless otherwise specified. All organic solvents in analytical grade (99%) were purchased from Sigma-Aldrich. The 1-octadecanethiol was purchased from Sigma-Aldrich (>98% purity). High purity eutectic gallium-indium (EGaIn; 99.99%) was obtained from Sigma-Aldrich and used as supplied.

Choice of Electrodes

Template-stripped Au surfaces (AuTS) served as bottom electrodes. Molecules (i.e., S(CH)11BPy) align on the Au surface, and form SAMs. The surface roughness and defects can increase the variance in the measured tunneling current or result in more frequent electrical shorts. We, thus, used ultraflat AuTS to minimize the defects of the surface, and the root-mean-square roughness for AuTS surface was 5.1 ± 0.4 nm (over an area of 25 μm2). GaOx/EGaIn served as a top electrode which enables non-damaging soft contact, as well as the simple and rapid measurement of current density. A native oxide layer (a few atomic layers thick) of EGaIn results in the non-Newtonian character of the GaOx/EGaIn liquid metal: GaOx/EGaIn maintains a conical shape (which is not a minimum in the surface energy) and behaves as a solid that yields at a critical stress. These features (i) enables measurements under ambient conditions, and (ii) prevents the SAMs from being damaged by the contact, resulting in high yield (70-90%).
Preparation of BIPY-MCl$_2$ Junctions

Our synthesis of the BIPY-containing SAMs, which consists of an insulating alkyl chain terminated by a BIPY moiety, followed a procedure from the literature.$^5$ SAMs of S(CH$_2$)$_{11}$BIPY were formed by immersion of a smooth template-stripped (TS) gold surface (Au$^{\text{TS}}$) in 1.0 mM ethanolic solutions of thiol-terminated molecules for 18 hours under a nitrogen atmosphere. The BIPY moieties were complexed with metal (II) chlorides by incubating the SAM within a 10-mM solution of metal (II) chloride in ethanol to form Au$^{\text{TS}}$-S(CH$_2$)$_{11}$BIPY-MCl$_2$ junctions, also under a nitrogen atmosphere for 18 hours. After each immersion, we gently rinsed the samples with ethanol for one minute (~1 ml/min) to remove residue on the surface and dried the samples under a slow flow of nitrogen gas. In BIPY-MCl$_2$ junctions, metal(II) complexed with SAMs of alkanethiolates terminated by 2,2'-bipyridine (Au$^{\text{TS}}$-S(CH$_2$)$_{11}$BIPY-M) with 1:1 stoichiometry. To minimize uncertainties, (i) all the BIPY-MCl$_2$ junctions are complexed with metals which have the same principal quantum number, (ii) the oxidation state of metals in as-fabricated BIPY-MCl$_2$ junctions is +2, and (iii) the counterions are all chloride ions. BIPY-CoCl$_2$ and BIPY-CuCl$_2$ complex probably has a structure of distorted tetrahedral.$^6$–$^8$

Characterization: J–V Measurements

We performed the measurements within one hour of the samples being prepared. After placing the samples (Au$^{\text{TS}}$-S(CH$_2$)$_{11}$BIPY-M(II)Cl$_2^-$) on the anti-vibration table, we connected a grounded Au surface to the negative port of a source meter (6430 Sub-Femtoamp Remote SourceMeter, Keithley). A 10-μL Hamilton syringe containing eutectic indium-gallium (EGaIn, 75.5 % Ga 24.5 %, and superficial layer of GaO$_x$) alloy, serving as a top electrode, was
controlled by a micromanipulator, and was connected to the port of the source meter. We formed an EGaIn tip of conical shape by extruding an EGaIn drop from the syringe on a clean Si wafer, and bringing the EGaIn tip gently into contact with the samples (contact area ~ 900 μm²). A voltage was subsequently applied to the EGaIn tip (positive voltage corresponds to EGaIn oxidizing and negative voltage corresponds to EGaIn reducing), and current flowing across the junctions was measured (one trace from 0 V to +1.0 V to −1.0 V to 0 V).

XPS Measurements

We used XPS to characterize AuTS-S(CH₂)₇BIPY-M(II)Cl₂ with instruments located in the Center for Nanoscale System at Harvard University. The energy of the incident X-ray beam used by the Thermo Scientific K-Alpha XPS system is at 1486.6 eV. We recorded high-resolution XPS spectra of S 2p, C 1s, N 1s, Au 4f, and Metal 2p. We used a least-square algorithm to fit the peak with a pseudo-Voigt function (a linear combination of Lorentzian (30 %) and Gaussian (70 %) functions) using the XPSpeak software. The sloping background was modeled using a Shirley plus linear background correction. The pseudo-Voight functions is used because it is well-known that instrumental factors (e.g., resolution of the analyzer or monochromator) and experimental factors (e.g., surface roughness of the samples, vibrational effect, and polarization effects) manifest as Gaussian broadening of the ideally Lorentzian signals of photoelectrons.

We calculated elemental ratios from the ratios of integrated area of XPS spectrum, and expect the the observation of uncorrected atomic ratios of nitrogen to sulfur being higher than two (Table S1) is due to the probability of photoelectrons emitted from the sulfur atom reaching the detector being lower than that of nitrogen, due to the density and thickness of the SAMs. We
corrected the atomic ratios of nitrogen to sulfur with thickness of SAMs based on the exponential attenuation of signal intensity by the thickness of SAMs.\textsuperscript{14,15}

**Preparation of Junctions for Temperature-Dependence Experiments**

We follow the method reported in the literature for the fabrication of molecular junctions used in temperature-dependence experiments.\textsuperscript{16} The EGaIn tip was brought into contact gently with the samples (Au\textsuperscript{TS}-S(CH\textsubscript{2})\textsubscript{11}BIPY-M(II)Cl\textsubscript{2}), with the contact area of \(\sim 900 \mu\text{m}^2\). A drop of photocurable polymer (Norland Optical Adhesive 61, Norland Products) was placed on the sample near the EGaIn electrode to surround the Au\textsuperscript{TS}-S(CH\textsubscript{2})\textsubscript{11}BIPY-M(II)Cl\textsubscript{2}/Ga\textsubscript{2}O\textsubscript{3}/EGaIn by the photocurable polymer. As we exposed the junctions to UV light using a hand-held lamp for a few seconds (~5 s), the EGaIn electrode in conical shape was encapsulated with the cured polymer. Then, we gently lifted the syringe containing EGaIn to form encapsulated BIPY-MCl\textsubscript{2} junctions.

**Density-Functional Theory Calculations.**

Quantum chemical calculations were calculated at the DFT level using Nwchem 6.6\textsuperscript{17} software with the B3LYP hybrid functional. All calculations were performed using an open-shell configuration where the spin was specified. We performed initial calculations and optimization of the molecular geometries using the 6-311++* basis sets for H, C, N, and Cl atoms and lanl2dz effective core potentials (ecp) for the S, Co, and Cu atoms. After the geometry optimization, we performed DFT calculations with the aug-cc-pvdz basis sets for H, C, N, and Cl atoms and lanl2dz effective core potentials (ecp) for the S, Co, and Cu atoms. We visualized the DFT orbitals using Avogadro.\textsuperscript{18}
**Raman Spectroscopy**

To determine the effect of the applied potential on the molecular conformations of the BIPY-Co(II)Cl$_2$ junctions, we employed confocal Raman spectroscopy to measure the Raman spectrum of the SAMs. Raman measurements were carried out using a Horiba LabRam HR Evolution confocal Raman microscopy with 633 nm excitation (~10 mW). The Raman measurements were averaged over 25 spots on the SAMs with 5 measurements collected each for 300 s with a 150 um pinhole and 600 gr/mm grating. The spectra were corrected for stray cosmic rays, and the spectrograph was calibrated to a Si wafer (peak at 520.7 cm$^{-1}$) prior to each measurement. All spectra shown are subtracted for a bare Au sample. We performed Raman measurements by imaging through the Au layer on samples deposited on 30 nm template stripped-Au and encapsulated using optical adhesive. A voltage was applied to the SAM through the EGaIn electrode using a Keithley 2400.
Table S1. Elemental Ratios in the Au^{TS}-S(CH_{2})_{11}BIPY-M(II)Cl_{2} junctions (M = Cr, Mn, Fe, Co, Ni, and Cu) characterized by X-ray photoelectron spectroscopy (XPS). Experiments were replicated a total of ten times, and uncertainty values represent the standard deviation.

<table>
<thead>
<tr>
<th>BIPY-MCl_{2} junctions</th>
<th>Cr</th>
<th>Mn</th>
<th>Fe</th>
<th>Co</th>
<th>Ni</th>
<th>Cu</th>
</tr>
</thead>
<tbody>
<tr>
<td>Sulfur : Nitrogen</td>
<td>1 : 2.85 ± 0.04</td>
<td>1 : 2.90 ± 0.06</td>
<td>1 : 2.87 ± 0.08</td>
<td>1 : 2.74 ± 0.05</td>
<td>1 : 2.73 ± 0.08</td>
<td>1 : 2.72 ± 0.08</td>
</tr>
<tr>
<td>Metal : Nitrogen</td>
<td>1 : 2.20 ± 0.19</td>
<td>1 : 1.82 ± 0.18</td>
<td>1 : 1.86 ± 0.13</td>
<td>1 : 1.81 ± 0.14</td>
<td>1 : 2.24 ± 0.13</td>
<td>1 : 1.88 ± 0.12</td>
</tr>
<tr>
<td>Metal : Chloride</td>
<td>1 : 1.14 ± 0.11</td>
<td>1 : 1.34 ± 0.12</td>
<td>1 : 1.55 ± 0.09</td>
<td>1 : 1.85 ± 0.06</td>
<td>1 : 1.16 ± 0.07</td>
<td>1 : 1.72 ± 0.16</td>
</tr>
</tbody>
</table>
Fig. S1. Averaged J(V) traces of (a-f) Au^{TS}-S(CH_2)_11BIPY-MCl_2//GaO_x/EGaIn junctions (M = (a) Cr, (b) Mn, (c) Fe, (d) Co, (e) Ni, and (f) Cu).
**Fig. S2.** The ratio of conductance for the forward and reverse scan in (a) BIPY-Co and (b) BIPY-Cu junctions which complexed with halide anions. The error bars represent the standard deviation.
Figure S3. Fowler-Nordheim (FN) plots for junctions composed of alkanethiolates SAMs: $\text{Au}^{\text{TS}}$-$\text{S(CH}_2\text{)}_{15}\text{CH}_3$/$\text{GaO}_x$/$\text{EGaIn}$. Voltage window is -1.0 V to +1.0 V.
**Fig. S4.** The ratio of conductance for forward and reverse scan in BIPY-MCl$_2$ junctions complexed with (a) BIPY-Mn, Fe, Ni (a voltage window of ±0.1 V) and (b) BIPY-CrCl$_2$ junctions (a voltage window of ±1.5 V).
**Fig. S5.** The ratio of conductance for forward and reverse scan in BIPY-CoCl₂ junctions with the opposite direction of voltage sweep.
Fig. S6. Energy level diagrams (defined by LUMO of alkyl chain) in (a) direct and (b) FN tunneling conditions.
Fig. S7. The magnitude of hysteresis ($G_{\text{rev}}/G_{\text{fwd}}$) in BIPY-CoCl$_2$ junctions with the change in voltage window.
**Fig. S8.** HOMO and LUMO orbitals generated by DFT of BIPY-CuCl$_2$ and BIPY-CoCl$_2$ with no applied field and a field of 3 V/nm.
Fig. S9. Averaged plots of conductance per unit contact area in log-scale *versus* applied voltage traces measured in Co junctions measured at 300 K and 200 K.
**Fig. S10.** The ratio of conductance for forward and reverse scan in BIPY-CoCl$_2$ junctions with changing scan rate.
Fig. S11. Raman spectrum of BIPY-CoCl$_2$ at 0 V (black) and a potential of 1 V (blue) after excitation at 633 nm. Peaks at ~1300 cm$^{-1}$ and ~1240 cm$^{-1}$ correspond to in-plane ring modes.$^{19,20}$ Peaks at ~1450 cm$^{-1}$ correspond to CH deformation modes.$^{19,20}$ Peak at ~990 cm$^{-1}$ corresponds to a ring-breathing mode.$^{19,20}$
References


